

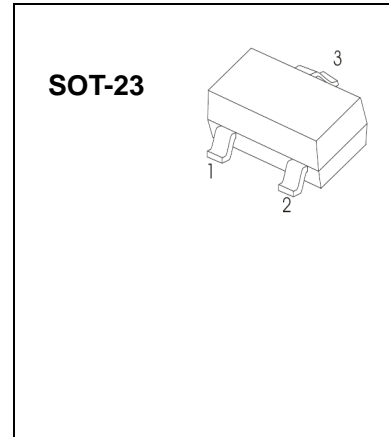
SOT-23 Plastic-Encapsulate Transistors

BC856

BC857

BC858

FEATURES



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

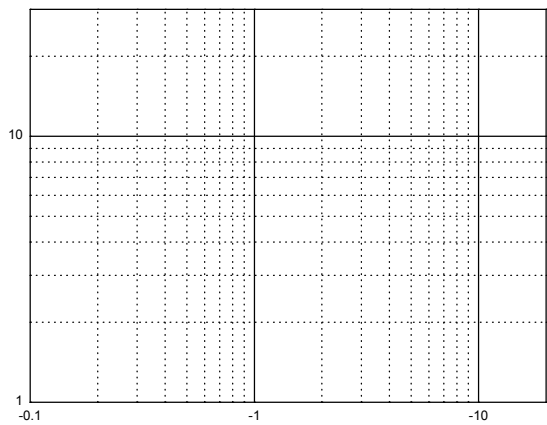
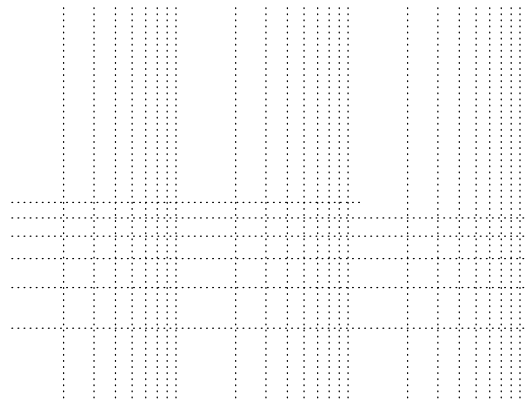
Symbol	Parameter	Value	Unit
V _{CB0}			
V _{CEO}			
V _{EBO}		-5	V
I _C			
P _C			mW
R _{JA}	Thermal Resistance From Junction To Ambient		°C/W
T _J			°C
T _{stg}		-65 +150	°C

DEVICE MARKING

BC856A=3A;BC856B=3B;
 BC857A=3E;BC857B=3F;BC857C=3G;
 BC858A=3J; BC858B=3K; BC858C=3L

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage BC856 BC857 BC858		μ			
Collector-emitter breakdown voltage BC856 BC857 BC858					
Emitter-base breakdown voltage		μ			
Collector cut-off current BC856 BC857 BC858					μ
Emitter cut-off current					μ
DC current gain BC856A, 857A,858A BC856B, 857B,858B BC857C,BC858C					
Collector-emitter saturation voltage					
Base-emitter saturation voltage					
Transition frequency					
Collector capacitance					



Note:
1. Controlling dimc

—
2000
1
—1000
—500